



#### 30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C		
-30V	$20m\Omega$ @ $V_{GS} = -10V$	004		
	$29m\Omega$ @ $V_{GS} = -5V$	-30A		

## **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

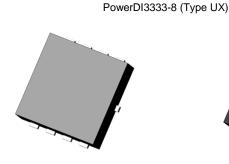
- Load Switch
- Power Management Functions

## **Features**

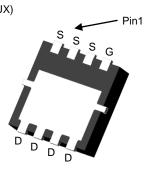
- Low R<sub>DS(ON)</sub> Ensures On State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

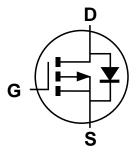
- Case: PowerDI<sup>®</sup>3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)







**Bottom View** 



**Equivalent Circuit** 

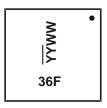
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3036SFV-7	PowerDI3333-8 (Type UX)	2000/Tape & Reel
DMP3036SFV-13	PowerDI3333-8 (Type UX)	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



36F = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 17 = 2017)

WW = Week Code (01 to 53)



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	-30	V	
Gate-Source Voltage	V <sub>GSS</sub>	±25	V	
Continuous Drain Current, V <sub>GS</sub> = -10V (Note 6)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-8.7 -7.0	Α
Continuous Drain Current, $V_{GS} = -10V$ (Note 7) $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$		Ι <sub>D</sub>	-30 -25	А
Maximum Continuous Body Diode Forward Current (Note 7)	Is	-3.6	Α	
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-80	Α	
Avalanche Current, L = 0.3mH (Note 8)	I <sub>AS</sub>	-17.5	А	
Avalanche Energy, L = 0.3mH (Note 8)	E <sub>AS</sub>	64	mJ	

# Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		$P_D$	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	137	°C/W
Total Power Dissipation (Note 6)	$P_{D}$	2.3	W	
Thermal Resistance, Junction to Ambient (Note 6)  Steady State		$R_{ heta JA}$	55	°C/W
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	3.5	10/00	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

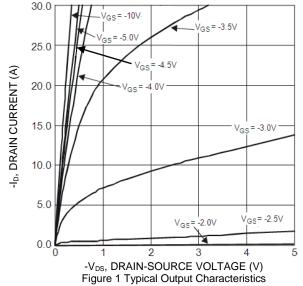
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

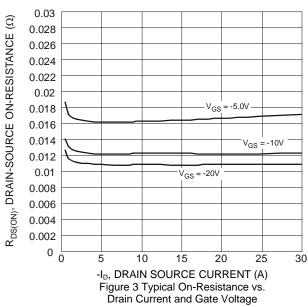
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	1	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	$V_{GS(TH)}$	-1.0		-2.5	٧	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D-s/s/		_	20	mΩ	$V_{GS} = -10V, I_D = -8A$	
Static Diam-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	29	11122	$V_{GS} = -5V, I_D = -5A$	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.2	٧	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	1931	_		V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V f = 1.0MHz	
Output Capacitance	Coss	_	226	_	pF		
Reverse Transfer Capacitance	Crss	_	168	_			
Gate Resistance	$R_{G}$	_	11	1	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = -5V)	$Q_g$	_	8.8	_			
Total Gate Charge (V <sub>GS</sub> = -10V)	$Q_g$	_	16.5	1	nC	\/ 15\/ I 10\	
Gate-Source Charge	$Q_{gs}$	_	2.6	1	IIC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -10A	
Gate-Drain Charge	$Q_{gd}$	_	3.6	1			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	8.2	1			
Turn-On Rise Time	t <sub>R</sub>	_	14		ns	$V_{DD} = -15V$ , $V_{GS} = -10V$ ,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	65	_	115	$R_{GEN} = 3\Omega$ , $I_D = -10A$	
Turn-Off Fall Time	t <sub>F</sub>	_	31.6	_			
Reverse Recovery Time	t <sub>RR</sub>	_	9.3	_	ns I OA JI/JI FOOA/		
Reverse Recovery Charge	$Q_{RR}$		12.2	_	nC	$I_F = -8A$ , di/dt = 500A/ $\mu$ s	

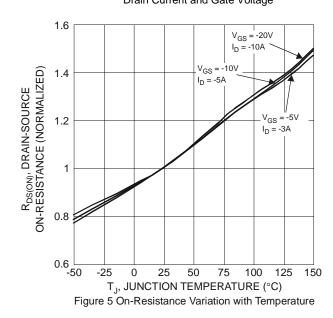
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.



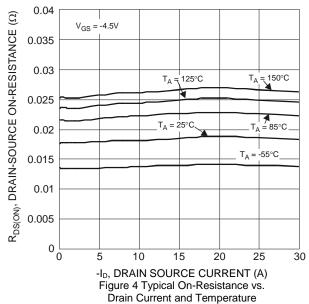








30  $V_{DS} = -5.0V$ 25 -I<sub>D</sub>, DRAIN CURRENT (A) 20 15 10 T<sub>A</sub> = 150°C T<sub>A</sub> = 85°C T<sub>A</sub> = 125°C 5  $T_A = 25^{\circ}C$ = -55°C 00  $\hbox{-V}_{\text{GS}}, \, \text{GATE-SOURCE} \, \hbox{VOLTAGE} \, \, (\text{V})$ Figure 2 Typical Transfer Characteristics



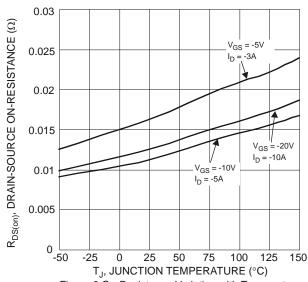


Figure 6 On-Resistance Variation with Temperature





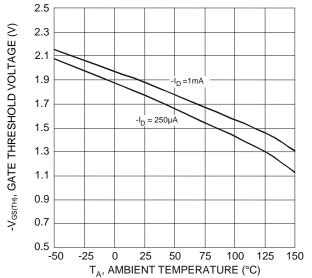


Figure 7 Gate Threshold Variation vs. Ambient Temperature

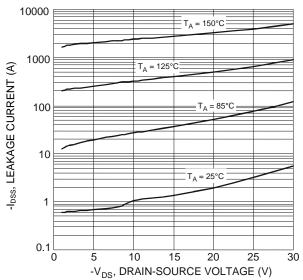
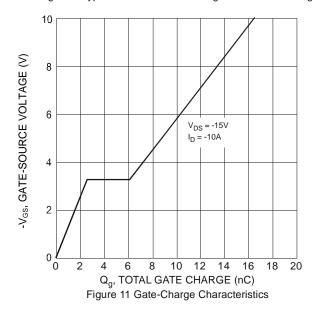
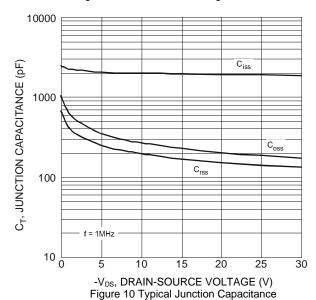


Figure 9 Typical Drain-Source Leakage Current vs. Voltage



30 V<sub>GS</sub>= 0V 25 -Is, SOURCE CURRENT (A) 20 15 T<sub>A</sub>= 150°C 10 <sub>A</sub>= 25°C 5 T<sub>A</sub>= -55°C 0 \_ 0.3 0.9 1.2 1.5

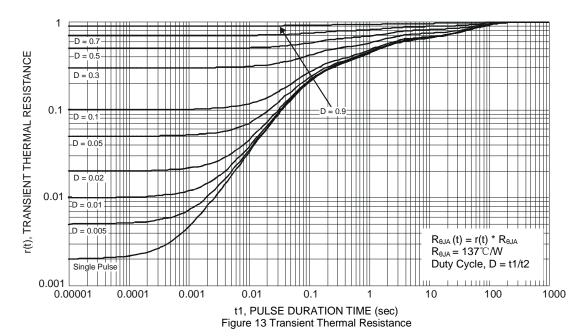
- $V_{\text{SD}}$ , SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current



100
R<sub>DS(ON)</sub>
Limited

10
P<sub>W</sub>= 10s
P<sub>W</sub>= 10s
P<sub>W</sub>= 10ms
P<sub>W</sub>= 10m





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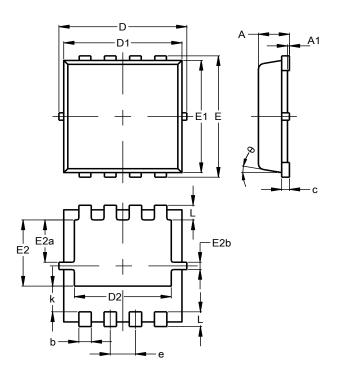
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## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UX)

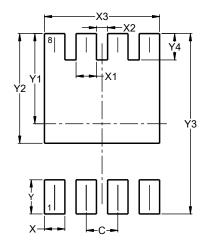


PowerDI3333-8 (Type UX)				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A1	0.00	0.05		
b	0.25	0.40	0.32	
С	0.10	0.25	0.15	
D	3.20	3.40	3.30	
D1	2.95	3.15	3.05	
D2	2.30	2.70	2.50	
Е	3.20	3.40	3.30	
E1	2.95	3.15	3.05	
E2	1.60	2.00	1.80	
E2a	0.95	1.35	1.15	
E2b	0.10	0.30	0.20	
е	0.65 BSC			
k	0.50	0.90	0.70	
Ĺ	0.30	0.50	0.40	
θ	0°	12°	10°	
All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UX)



Dimensions	value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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